

Plastic-Encapsulate Transistors

DUAL TRANSISTOR (NPN+NPN)

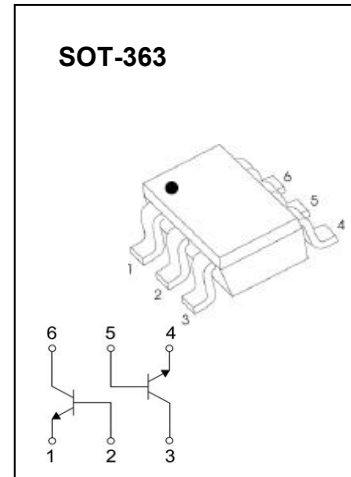
FEATURES

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors

MARKING: BC846ADW 4At

BC846BDW 4Bt

BC846CDW 4Gt



MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	65	V
V_{EBO}	Emitter-Base Voltage	6	V
I_c	Collector Current –Continuous	0.1	A
P_c	Collector Dissipation	200	mW
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	65			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=70V, I_E=0$			100	nA
Emitter cut-off current	I_{EBO}	$I_C=0, V_{EB}=5V$			100	nA
DC current gain	h_{FE}	$V_{CE}=5V, I_C=2mA$	A	110	220	
			B	200	450	
			C	420	800	
Collector-emitter saturation voltage	$V_{CE(sat)(1)}$	$I_C=10mA, I_B=0.5mA$			0.25	v
	$V_{CE(sat)(2)}$	$I_C=100mA, I_B=5mA$			0.5	v
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100mA, I_B=5mA$			1.1	v
Transition frequency	f_T	$V_{CB}=5V, I_E=10mA, f=100MHz$	100			MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$			1.5	pF



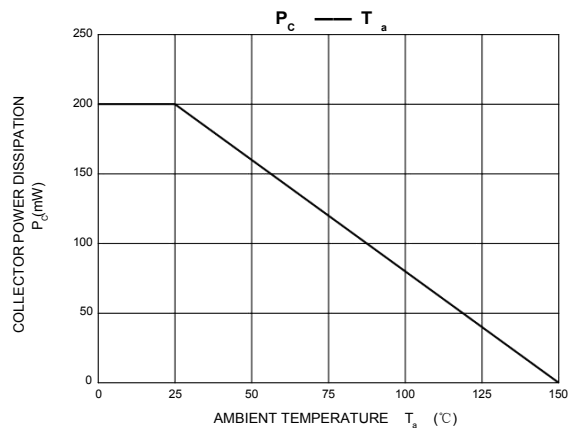
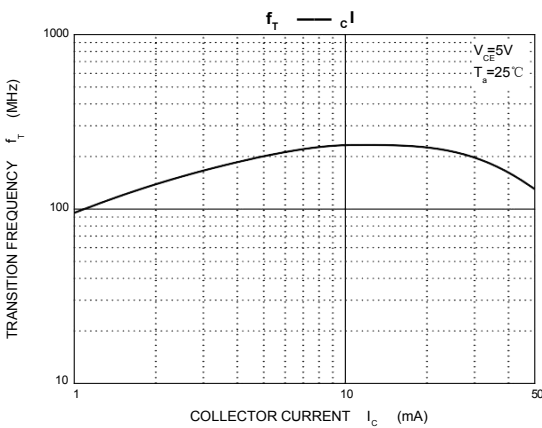
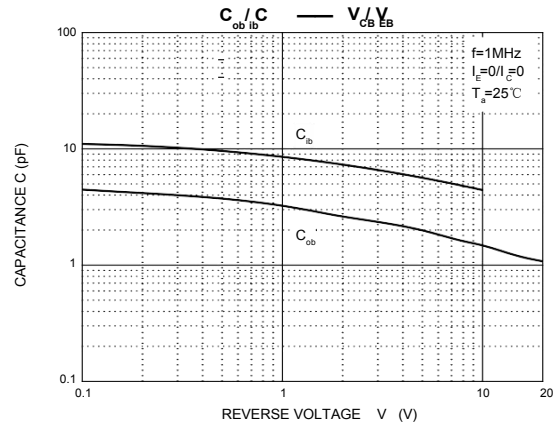
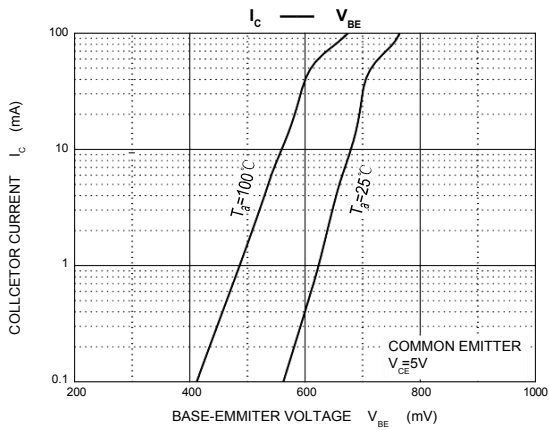
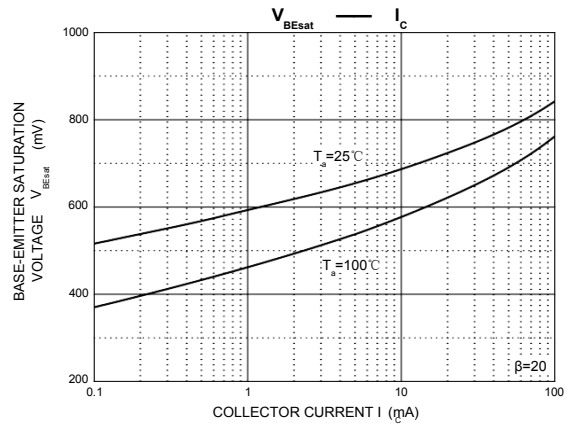
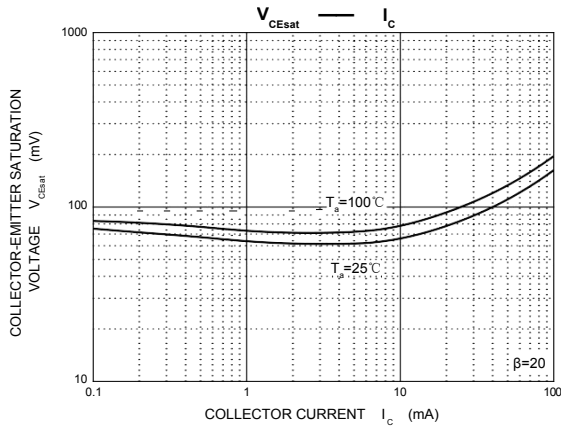
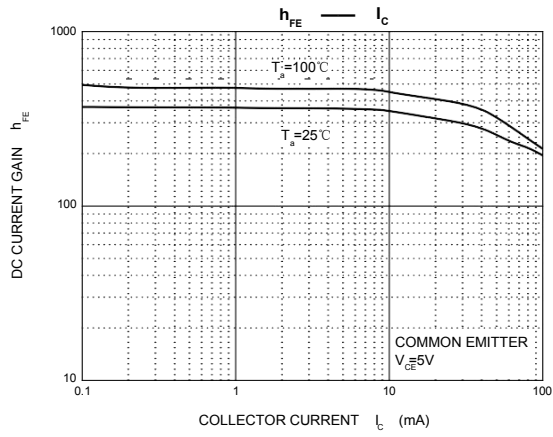
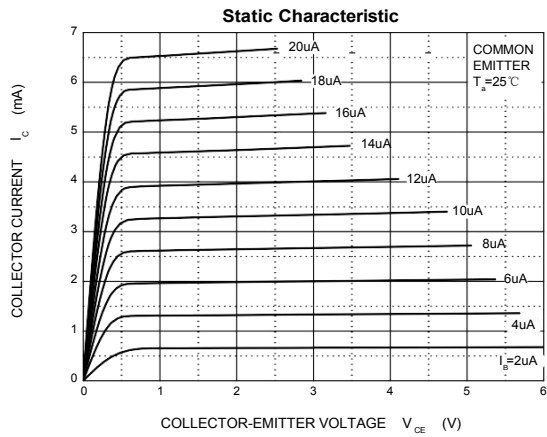
CHINA BASE
INTERNATIONAL

SOT-363



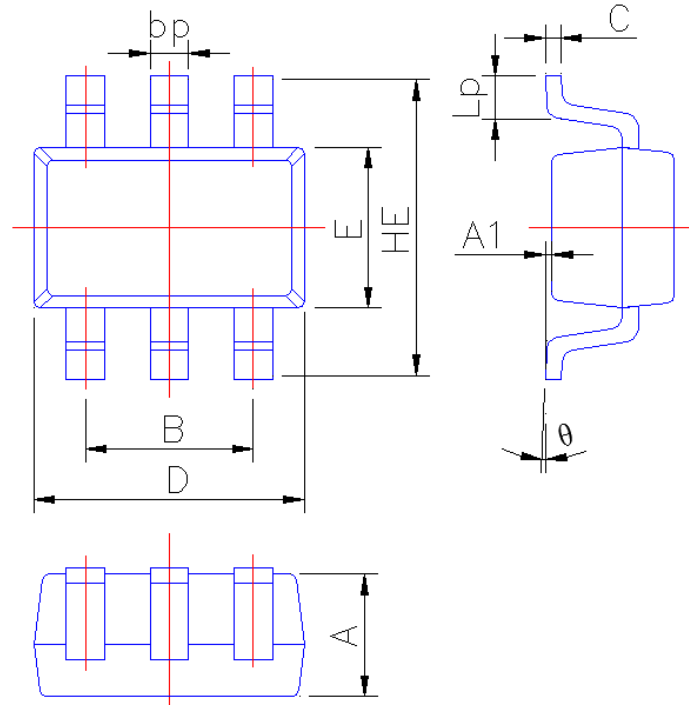
BC846ADW/BC846BDW/BC846CDW

www.china-base.com.hk





SOT-363 Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
θ	0°	6°